



UTT80N08

Preliminary

Power MOSFET

**80A, 80V N-CHANNEL
POWER MOSFET**

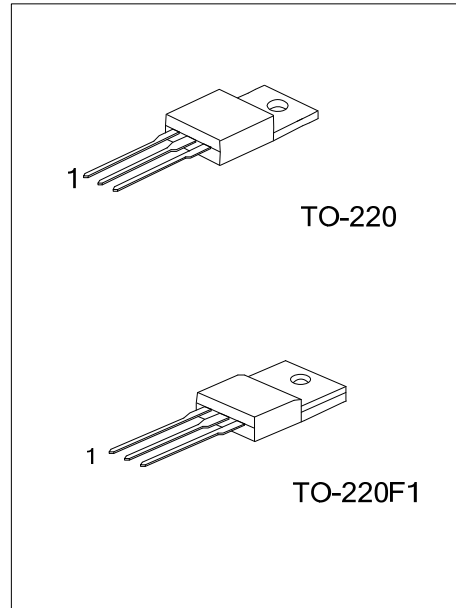
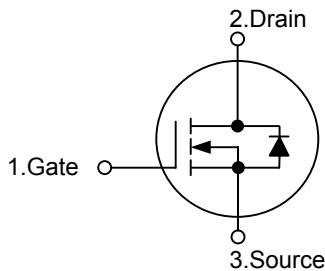
■ DESCRIPTION

The UTC **UTT80N08** is an N-channel MOSFET using UTC advanced technology. It can be used in applications, such as power supply (secondary synchronous rectification), industrial and primary switch etc.

■ FEATURES

* Trench FET Power MOSFETS Technology

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT80N08L-TA3-T	UTT80N08G-TA3-T	TO-220	G	D	S	Tube
UTT80N08L-TF1-T	UTT80N08G-TF1-T	TO-220F1	G	D	S	Tube

Note: G: GND, D: Drain, S: Source

<p>UTT80N08G-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Halogen Free</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF1: TO-220F1</p> <p>(3) L: Lead Free, G: Halogen Free</p>
---	---

■ ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	80	A
Pulsed Drain Current	I_{DM}	320	A
Avalanche Energy, Single Pulse	E_{AS}	320	mJ
Power Dissipation	TO-220	137	W
	TO-220F1	70	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

$L=0.1\text{mH}$, $I_{AS}=80\text{A}$, $V_{DD}=25\text{V}$, $R_G=20\Omega$, Starting $T_J=25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C/W}$
Junction to Case	TO-220	0.91	$^\circ\text{C/W}$
	TO-220F1	1.77	

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	80			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80\text{V}$, $V_{GS}=0\text{V}$		0.01	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$		± 1	± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.1		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=80\text{A}$			12	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		4700		pF
Output Capacitance	C_{OSS}			1260		pF
Reverse Transfer Capacitance	C_{RSS}			580		pF
SWITCHING PARAMETERS						
Gate to Source Charge	Q_{GS}	$V_{DD}=60\text{V}$, $V_{GS}=0\sim 10\text{V}$, $I_D=80\text{A}$		25	37	nC
Gate to Drain Charge	Q_{GD}			69	116	nC
Total Gate Charge	Q_G			144	180	nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=40\text{V}$, $R_G=2.2\Omega$ $I_D=80\text{A}$, $V_{GS}=10\text{V}$		26		ns
Rise Time	t_R			50		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			61		ns
Fall-Time	t_F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				80	A
Pulsed Current	I_{SM}				320	
Drain-Source Diode Forward Voltage	V_{SD}	$I_{SD}=80\text{A}$		0.9	1.3	V

Note: 1. Defined by design. Not subject to production test.

2. Qualified at -20V and +20V.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.